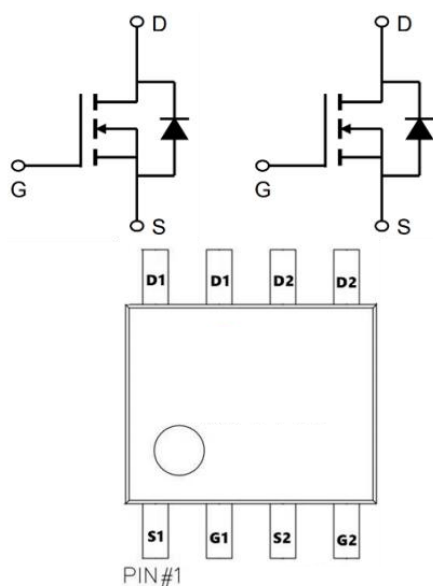


Description

The SX8H06S uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



General Features

$V_{DS} = 60V$ $I_D = 8A$

$R_{DS(ON)} < 32m\Omega$ @ $V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply

SOP-8



Absolute Maximum Ratings ($T_c=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_A=25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	8.2	A
$I_D @ T_A=70^\circ C$	Continuous Drain Current, $V_{GS} @ 10V^1$	5.8	A
I_{DM}	Pulsed Drain Current ²	16.6	A
E_{AS}	Single Pulse Avalanche Energy ³	28.5	mJ
I_{AS}	Avalanche Current	22.6	A
$P_D @ T_A=25^\circ C$	Total Power Dissipation ⁴	1.5	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	85	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	36	$^\circ C/W$

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ.	Max	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V , I _D =250uA	60	66	---	V
ΔBVDSS/ΔT _J	BV _{DSS} Temperature Coefficient	Reference to 25°C , I _D =1mA	---	0.063	---	V/°C
RDS(ON)	Static Drain-Source On-Resistance ²	V _{GS} =10V , I _D =8A	---	23	32	mΩ
		V _{GS} =4.5V , I _D =6A	---	28	38	
VGS(th)	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.2	1.6	2.5	V
ΔVGS(th)	VGS(th) Temperature Coefficient		---	-5.24	---	mV/°C
IDSS	Drain-Source Leakage Current	V _{DS} =48V , V _{GS} =0V , T _J =25°C	---	---	1	uA
		V _{DS} =48V , V _{GS} =0V , T _J =55°C	---	---	5	
IGSS	Gate-Source Leakage Current	V _{GS} =±20V , V _{DS} =0V	---	---	±100	nA
gfs	Forward Transconductance	V _{DS} =5V , I _D =4A	---	21	---	S
R _g	Gate Resistance	V _{DS} =0V , V _{GS} =0V , f=1MHz	---	3.2	6.4	Ω
Q _g	Total Gate Charge (4.5V)	V _{DS} =48V , V _{GS} =4.5V , I _D =4A	---	12.6	---	nC
Q _{gs}	Gate-Source Charge		---	3.2	---	
Q _{gd}	Gate-Drain Charge		---	6.3	---	
Td(on)	Turn-On Delay Time	V _{DD} =30V , V _{GS} =10V , R _G =3.3Ω , I _D =4A	---	8	---	ns
T _r	Rise Time		---	14.2	---	
Td(off)	Turn-Off Delay Time		---	24.4	---	
T _f	Fall Time		---	4.6	---	
Ciss	Input Capacitance	V _{DS} =15V , V _{GS} =0V , f=1MHz	---	1378	---	pF
Coss	Output Capacitance		---	86	---	
Crss	Reverse Transfer Capacitance		---	64	---	
IS	Continuous Source Current ^{1,5}	V _G =V _D =0V , Force Current	---	---	4.8	A
ISM	Pulsed Source Current ^{2,5}		---	---	9.6	A
VSD	Diode Forward Voltage ²	V _{GS} =0V , I _S =1A , T _J =25°C	---	0.746	1.2	V

Note :

1.The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.

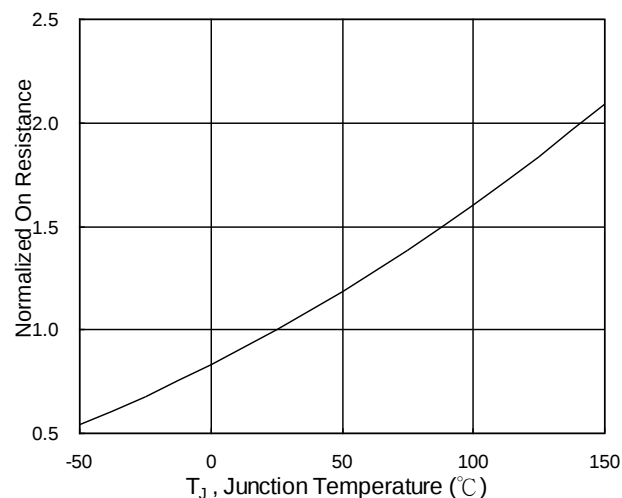
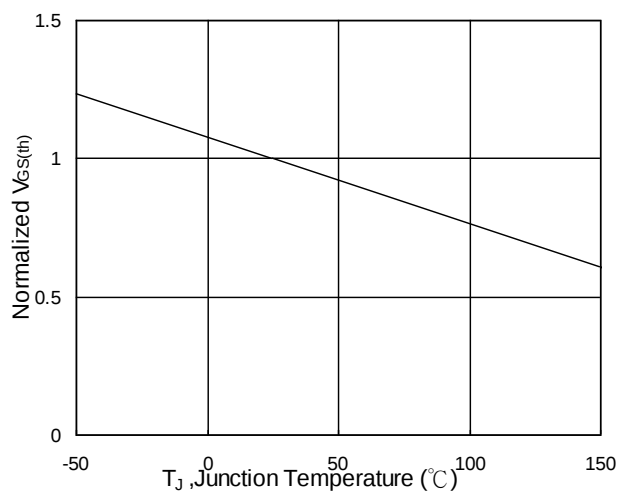
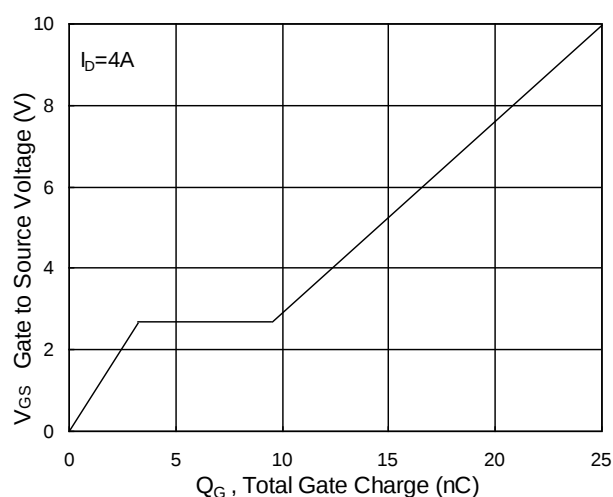
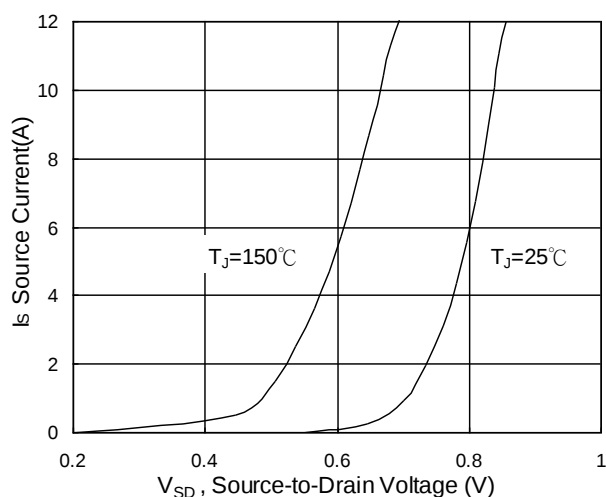
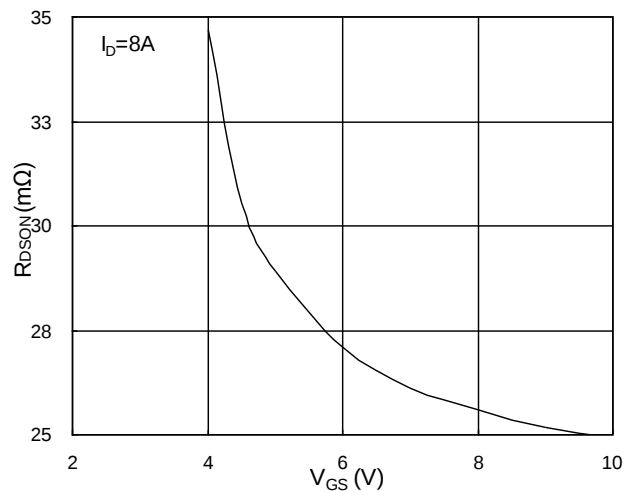
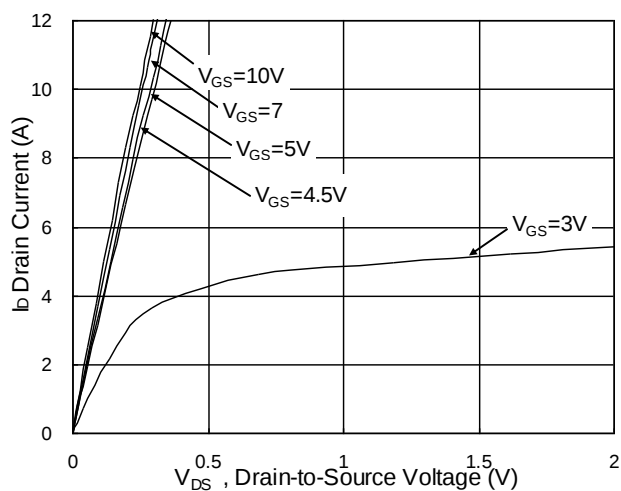
2.The data tested by pulsed , pulse width ≤ 300us , duty cycle ≤ 2%

3.The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=22.6A

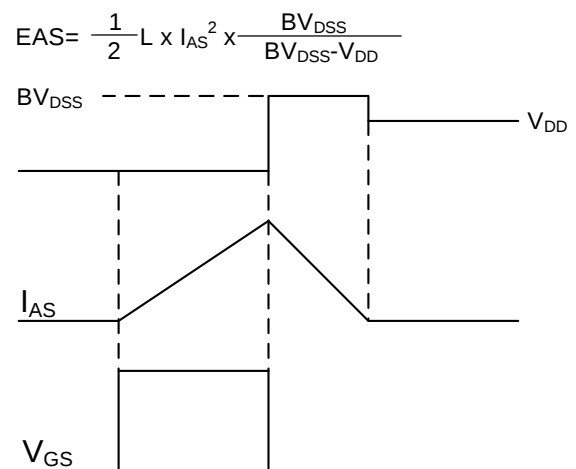
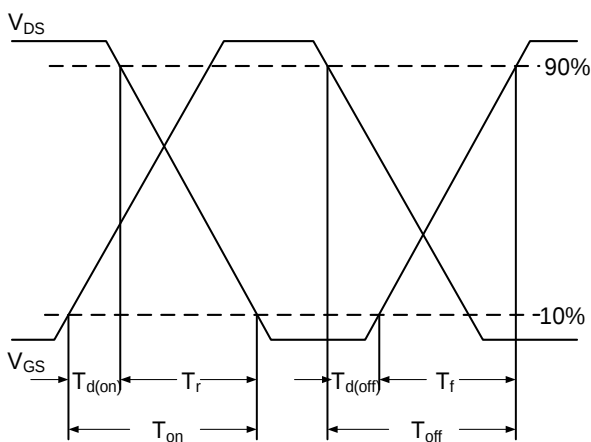
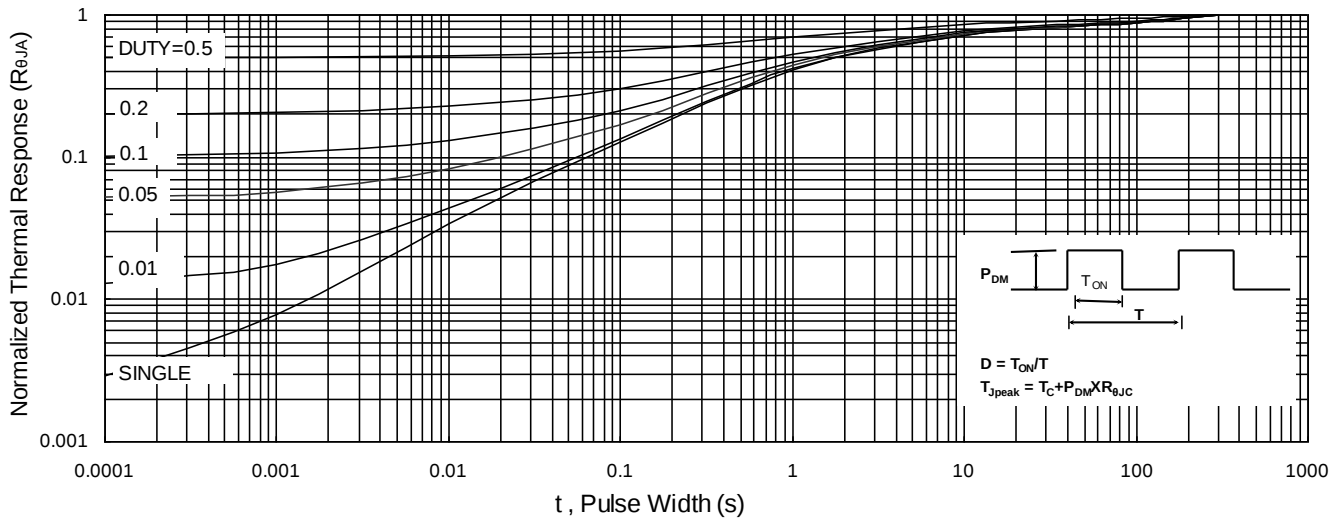
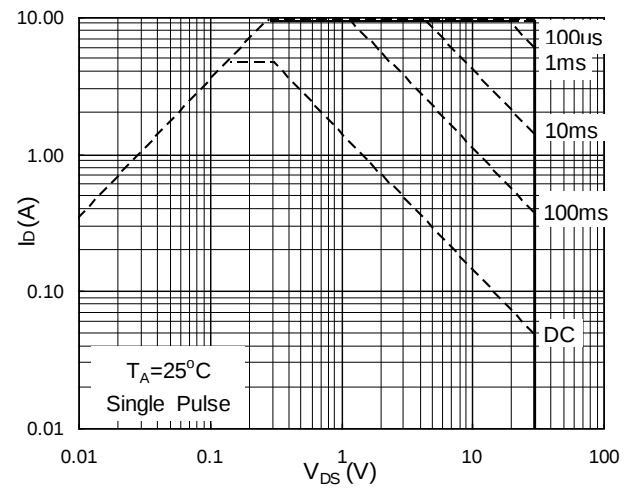
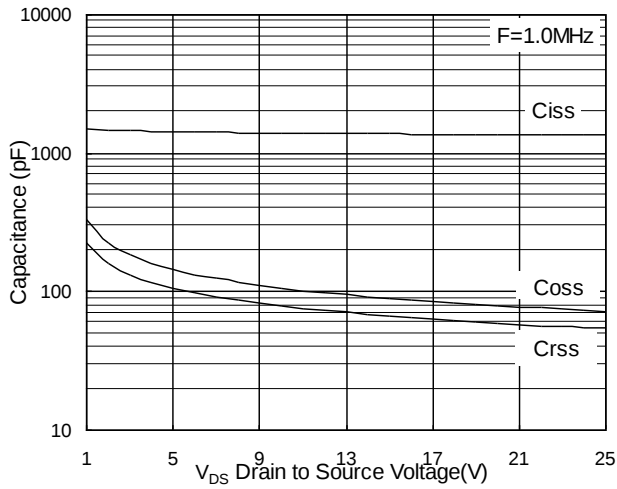
4.The power dissipation is limited by 150°C junction temperature

5.The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

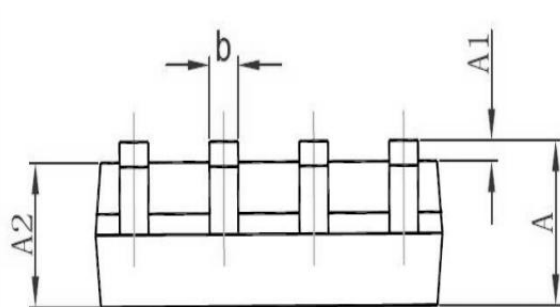
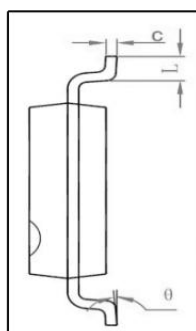
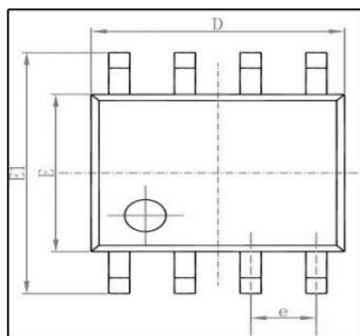
Typical Characteristics



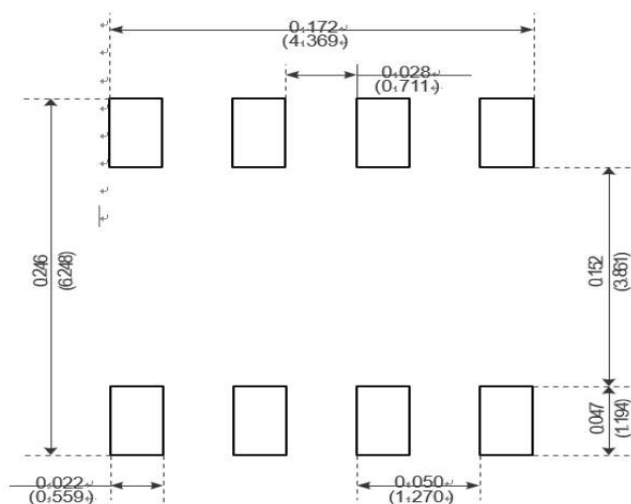
Typical Characteristics



Package Mechanical Data-SOP-8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 (BSC)		0.050 (BSC)	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	SOP-8		3000